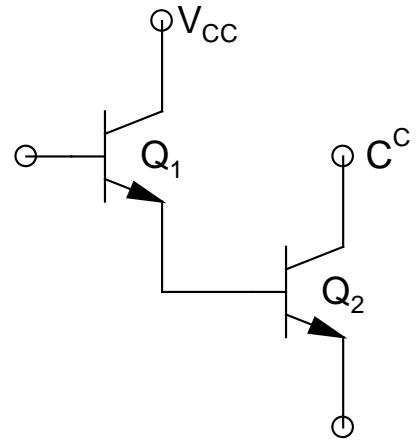


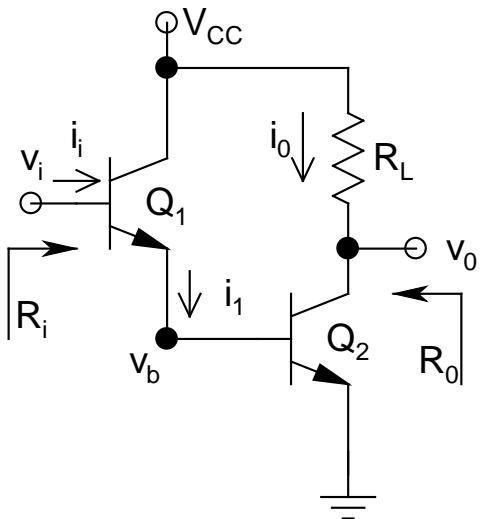
Compound Connections

- *Multi-Stage*
- Have some *special properties*
- *Popular Topologies*:
 - *Darlington*
 - *Cascade*
 - *DP* (or *DA*)
- *Modules by themselves*

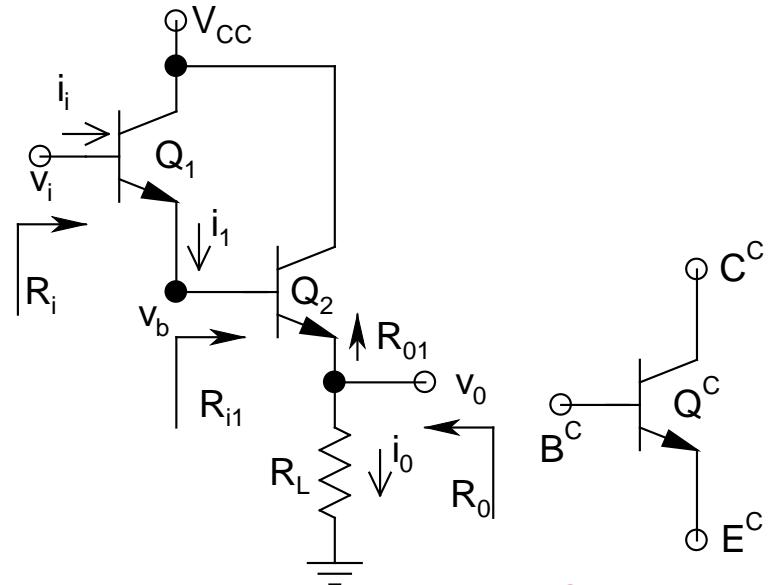
- **Darlington:**
 - Cascade of a **CC** stage, followed by either a **CE** or a **CC** stage
 - ***Two biggest advantages:***
 - ***Extremely large R_i***
 - ***Extremely large A_i***
 - ***These two advantages are automatic for MOS stages***
⇒ ***MOS Darlington has no special use***



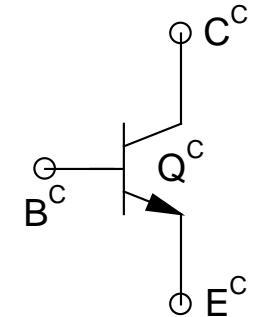
Generic Circuit



CC-CE Stage



CC-CC Stage



Compact Representation

➤ For ***DC biasing***:

$$I_{C2} = \beta_2 I_{B2} = \beta_2 I_{E1} \approx \beta_2 I_{C1}$$

$$\Rightarrow r_{\pi 2} = \beta_2 r_{E2} = \beta_2 V_T / I_{C2} = V_T / I_{C1} = r_{E1}$$

➤ For *ac analysis*:

CC-CE:

- $i_1 = (\beta_1 + 1)i_i$ and $i_0 = \beta_2 i_1 = \beta_2(\beta_1 + 1)i_i$
 $\Rightarrow A_i = i_0/i_i = \beta_2(\beta_1 + 1) \approx \beta^2$ (*Huge!*)
- $R_i = r_{\pi 1} + (\beta_1 + 1)r_{\pi 2} \approx 2r_{\pi 1}$
❖ $I_{C2} \sim mA$, $I_{C1} \sim 10s$ of μA , $r_{E1} \sim k\Omega$, $r_{\pi 1} \sim 100s$ of $k\Omega$ (*Huge!*)
- $v_0/v_b = -R_L/r_{E2}$ and $v_b/v_i = r_{\pi 2}/(r_{\pi 2} + r_{E1}) = 1/2$
 $\Rightarrow A_v = v_0/v_i = -R_L/(2r_{E2})$ (*Moderate*)
- $R_0 = R_L || r_{02} \approx R_L$ (*Moderate*)

➤ Thus, this stage has *huge A_i and R_i* , and
moderate A_v and R_0

➤ For *ac analysis*:

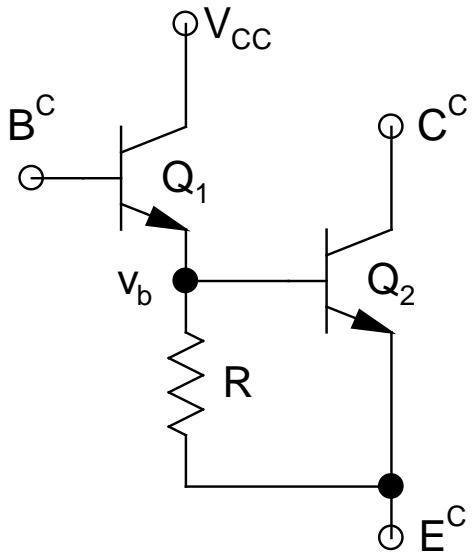
CC-CC:

- $i_1 = (\beta_1 + 1)i_i$ and $i_0 = (\beta_2 + 1)i_1 = (\beta_2 + 1)(\beta_1 + 1)i_i$
 $\Rightarrow A_i = i_0/i_i = (\beta_2 + 1)(\beta_1 + 1) \approx \beta^2$ (*Huge!*)
- $R_i = r_{\pi 1} + (\beta_1 + 1)(\beta_2 + 1)(r_{E2} + R_L)$
 $\approx r_{\pi 1} + \beta^2(r_{E2} + R_L)$ (*Astronomical!*)
- $R_{i1} = r_{\pi 2} + (\beta_2 + 1)R_L$
- $v_0/v_b = R_L/(R_L + r_{E2})$
- $v_b/v_i = R_{i1}/(r_{E1} + R_{i1})$
- $A_v = v_0/v_i \approx \beta_2 R_L / (2r_{E1} + \beta_2 R_L)$ (*Show!*)

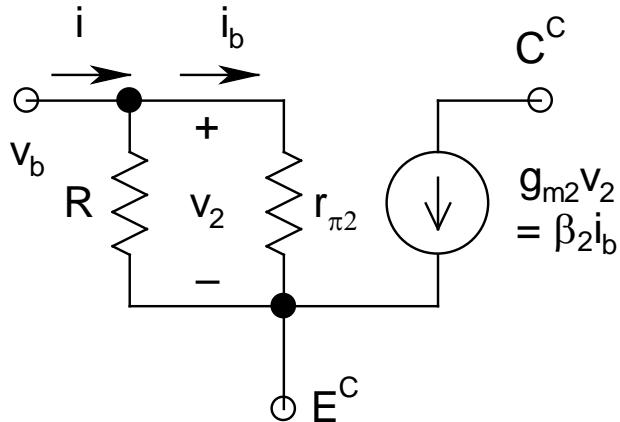
➤ Thus, this stage has *extremely large A_i and R_i* ,
and *A_v is ≤ 1 with no phase shift*

- $R_0 = R_L \parallel R_{01}$
 $R_{01} = r_{E2} + r_{E1}/(\beta_2 + 1)$ (*by inspection*)
 $\approx 2r_{E2}$
 $\Rightarrow R_0 \approx R_L \parallel (2r_{E2})$ (*Small*)
- Above analysis is *pretty straightforward*, and
assumes that both β_1 and β_2 are high
- *In reality, Q_1 operates with a very low value of I_C ($\sim 10s$ of μA)*
 $\Rightarrow \beta_1$ would drop significantly from its nominal value \Rightarrow Full advantage of the circuit can't be exploited

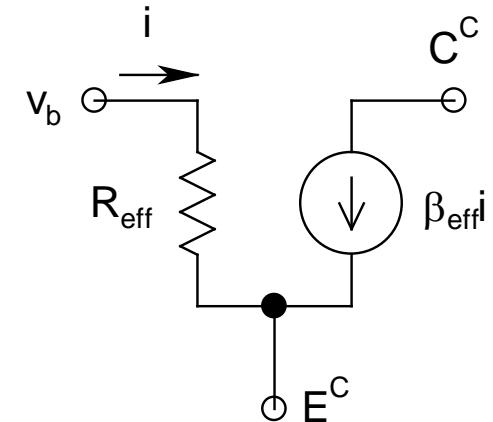
- *Need to jack up β_1*
- ❖ *How about using a keep-alive resistor?*



Darlington with
Keep-Alive Resistor R



ac Midband Equivalent
of Q_2 - R Combination



Simplified Equivalent
of Q_2 - R Combination

- ***R drains a constant DC current of $\sim 0.7/R$***
- ***This current is supplied by Q_1 , along with I_{B2}***
 $\Rightarrow I_{C1} \uparrow \Rightarrow \beta_1 \uparrow$
- ***However, this technique also changes β_2***
- ***Analysis:***

$$i_b = iR/(R + r_{\pi 2})$$

$$\Rightarrow i_c = \beta_2 i_b = \beta_2 iR/(R + r_{\pi 2}) = g_m r_{\pi 2} iR/(R + r_{\pi 2}) = g_m (R || r_{\pi 2}) i = g_m R_{eff} i = \beta_{eff} i$$

$$\beta_{eff} = g_m R_{eff} < \beta_2 \quad (R_{eff} = R || r_{\pi 2})$$

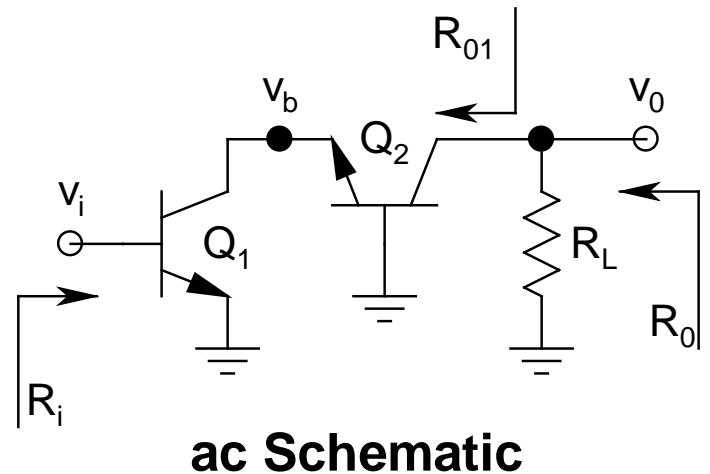
- As if $r_{\pi 2, eff} = R_{eff}$

- ***npn Cascode:***

- ***CE, followed by CB***
- Known as ***Wideband Amplifier***, due to its ***superior frequency response characteristic***

- ***Generally, both Q_1 and Q_2 are biased with the same I_C***
- ***Assuming Q_1 - Q_2 have same β :***

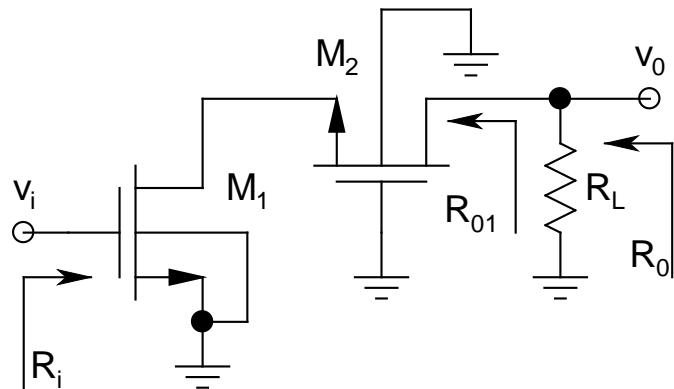
$$r_{E1} = r_{E2} = r_E \text{ and } r_{\pi 1} = r_{\pi 2} = r_\pi$$



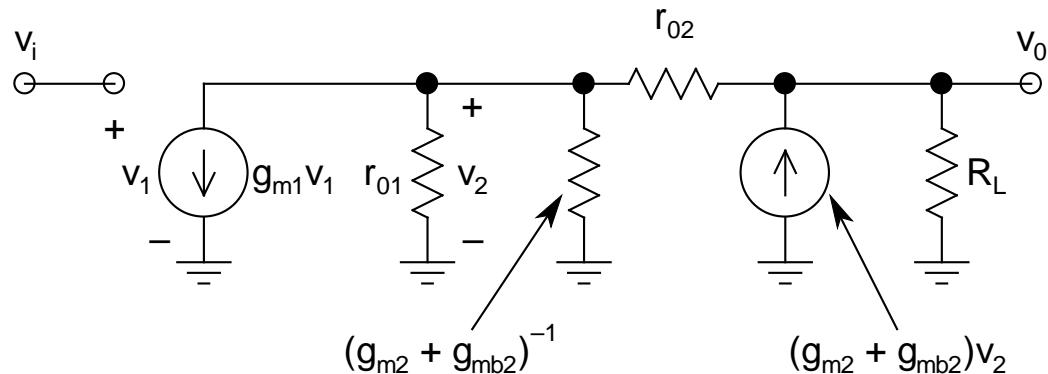
- *This circuit can be analyzed by inspection*
- $R_i = r_{\pi 1}$
- $v_0/v_b = +g_m R_L = R_L/r_{E2}$ (*CB Stage*)
- $v_b/v_i = -r_{E2}/r_{E1} = -1$
 - *CE Stage with R_i of Q_2 ($= r_{E2}$) as its load*
- Thus, $A_v = v_0/v_i = -R_L/r_{E2}$
- *Note that A_v is same as that for a CE stage, however, the bandwidth of this circuit is far superior than a CE stage*

- $R_o = R_L \parallel R_{01}$
- *If r_0 is neglected*, then $R_{01} \rightarrow \infty$ (*why?*)
- *If r_0 is included*, then $R_{01} = \beta r_{02}$ (*very high*)
- However, *it comes in parallel with R_L*
 \Rightarrow *Overall R_o is still $\sim R_L$*
- *Summary*:
 - *Moderate voltage gain*
 - *Moderate input resistance*
 - *Potential of having very large output resistance*
 - *Extremely large bandwidth*
 - *Preferred over a simple CE stage*

- **NMOS Cascode:**



ac Schematic



ac Midband Equivalent

- CS, followed by CG
- Generally, both M_1 and M_2 are biased with the same I_D
- M_1 does not have body effect, but M_2 has

- *By inspection*, $R_i \rightarrow \infty$ and $R_0 = R_L || R_{01}$
- *With r_{02} present, the analysis becomes a little complicated* \Rightarrow *neglect r_{02}* $\Rightarrow R_0 = R_L$
- *Neglecting r_{02} :*

$$v_0 = (g_{m2} + g_{mb2})v_2 R_L$$

$$v_2 = - g_{m1} v_1 / (g_{m2} + g_{mb2} + g_{01}) \quad (g_{01} = 1/r_{01})$$

$$\approx - g_{m1} v_1 / (g_{m2} + g_{mb2})$$

[since, in general, $g_{01} \ll (g_{m2} + g_{mb2})$]

$$\Rightarrow A_v = v_0/v_i = - g_{m1} R_L \quad (\text{since } v_1 = v_i)$$

- *This is same as the CS stage, however, here broad-banding is happening!*

- *A_v gets affected a little if r_{01} and r_{02} were included*
 - *Since r_{01} comes in parallel with $(g_{m2} + g_{mb2})^{-1}$, its effect on A_v is less pronounced than that of r_{02}*
 - *By inspection:*
- $$R_{01} \approx (g_{m2} + g_{mb2})r_{01}r_{02} \text{ (*Show!*)}$$
- *Note that if either of r_{01} or $r_{02} \rightarrow \infty$, $R_{01} \rightarrow \infty$ (*Why?*)*